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December 2013

FQP5N60C / FQPF5N60C

N-Channel QFET® MOSFET

600 V, 4.5 A, 2.5 Ω

Description

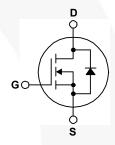
This N-Channel enhancement mode power MOSFET is • 4.5 A, 600 V, $R_{DS(on)}$ = 2.5 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 15 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 6.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 2.25 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP5N60C	FQPF5N60C	Unit
V _{DSS}	Drain-Source Voltage		600		V
I _D	Drain Current - Continuous (T _C = 25°C)		4.5	4.5 *	Α
	- Continuous (T _C = 100°C)			2.6 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	18	18 *	Α
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note		210		mJ
I _{AR}	Avalanche Current	(Note 1)	4.5		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		10		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P_{D}	Power Dissipation (T _C = 25°C)		100	33	W
	- Derate above 25°C		0.8	0.26	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to	+150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		°C	

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP5N60C	FQPF5N60C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.25	3.79	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP5N60C	FQP5N60C	TO-220	Tube	N/A	N/A	50 units
FQPF5N60C	FQPF5N60C	TO-220F	Tube	N/A	N/A	50 units

Symbol	Parameter	Parameter Test Conditions		Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		0.6		V/°C
I _{DSS}	Zara Cata Valtaga Drain Current	V _{DS} = 600 V, V _{GS} = 0 V			1	μА
	Zero Gate Voltage Drain Current	V _{DS} = 480 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.25 A		2.0	2.5	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.25 A		4.7		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		55 6.5	72 8.5	pF pF pF
	ing Characteristics			40	20	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 300 \text{ V}, I_D = 4.5$		10 42	30	ns
t _r	Turn-On Rise Time	A, $R_G = 25 \Omega$			90	ns
t _{d(off)}	Turn-Off Delay Time Turn-Off Fall Time	(Note 4)		38 46	85 100	ns
t _f Q _g	Total Gate Charge	\/ - 490\/ I - 4.5.A		15	100	ns nC
	Gate-Source Charge	$V_{DS} = 480 \text{ V}, I_{D} = 4.5 \text{ A},$ $V_{GS} = 10 \text{ V}$	/	2.5		nC
Q _{gs} Q _{gd}	Gate-Drain Charge	(Note 4)		6.6		nC
∝ ga	Gate-Drain Ghaige	(note ly		0.0		110
	Source Diode Characteristics at		1			
I _S	Maximum Continuous Drain-Source Diode Forward Current				4.5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				18	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 4.5 A			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_S = 4.5 \text{ A,}$		300	//	ns
Q_{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		2.2		μC

Notes:1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 18.9 mH, I_{AS} = 4.5 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
3.1 I_{SD} \leq 4.5 A, di/dt \leq 200 A/ μ s , V_{DD} \leq BV $_{DSS}$, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

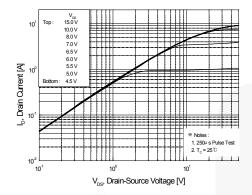


Figure 1. On-Region Characteristics

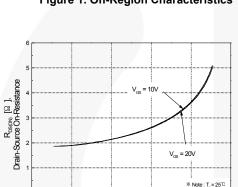


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

I_D, Drain Current [A]

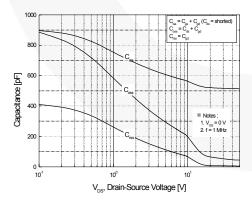


Figure 5. Capacitance Characteristics

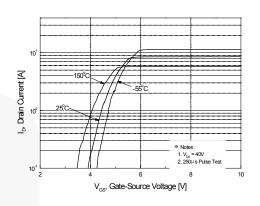


Figure 2. Transfer Characteristics

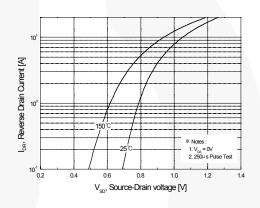


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

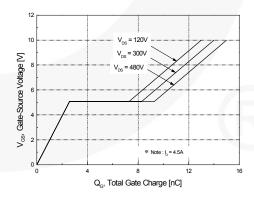


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

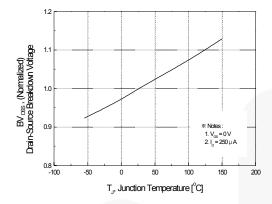


Figure 7. Breakdown Voltage Variation vs Temperature

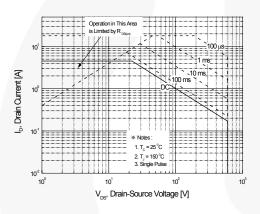


Figure 9-1. Maximum Safe Operating Area for FQP5N60C

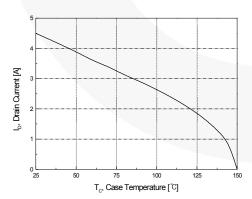


Figure 10. Maximum Drain Current vs Case Temperature

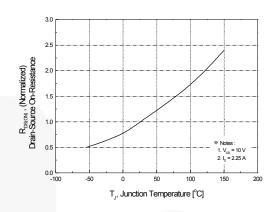


Figure 8. On-Resistance Variation vs Temperature

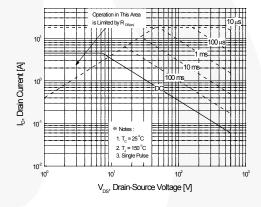


Figure 9-2. Maximum Safe Operating Area for FQPF5N60C

Typical Characteristics (Continued)

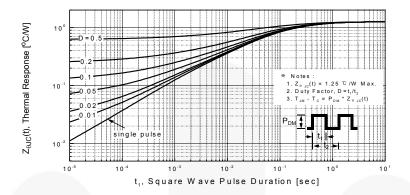


Figure 11-1. Transient Thermal Response Curve for FQP5N60C

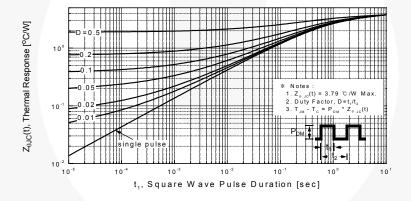


Figure 11-2. Transient Thermal Response Curve for FQPF5N60C

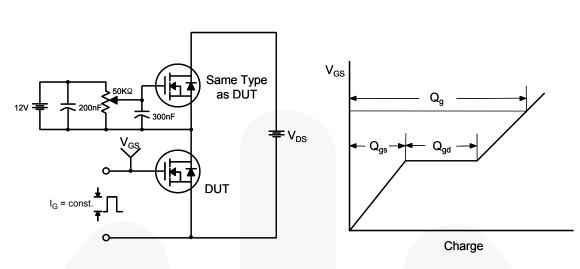


Figure 12. Gate Charge Test Circuit & Waveform

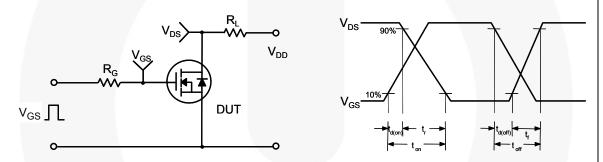


Figure 13. Resistive Switching Test Circuit & Waveforms

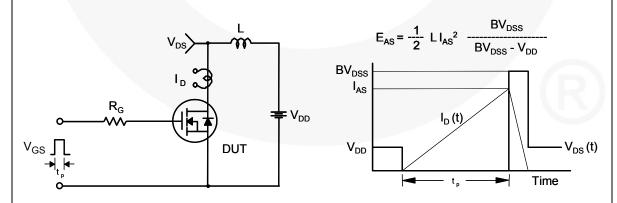
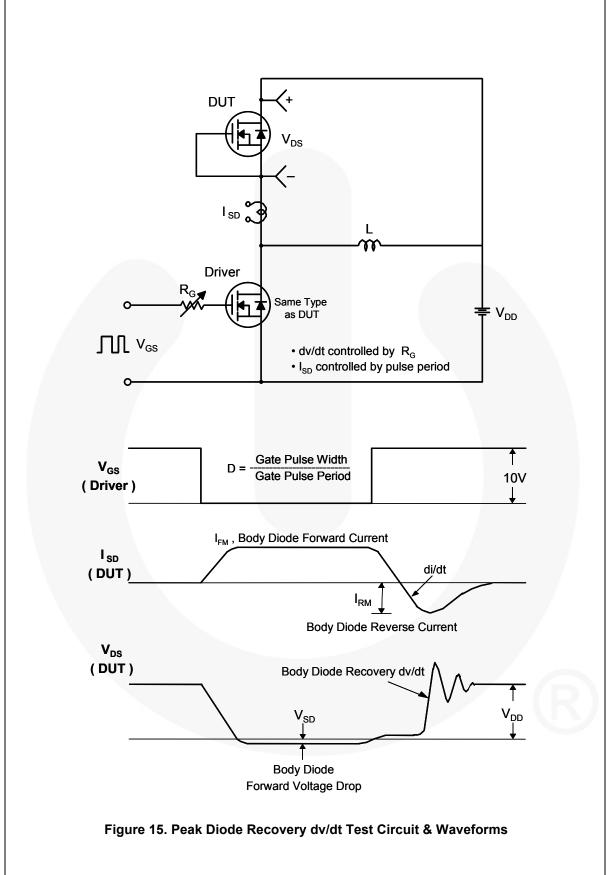


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

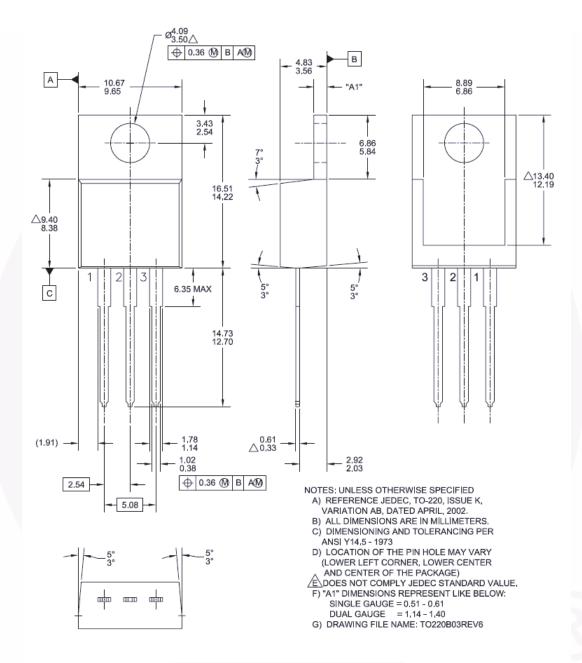


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

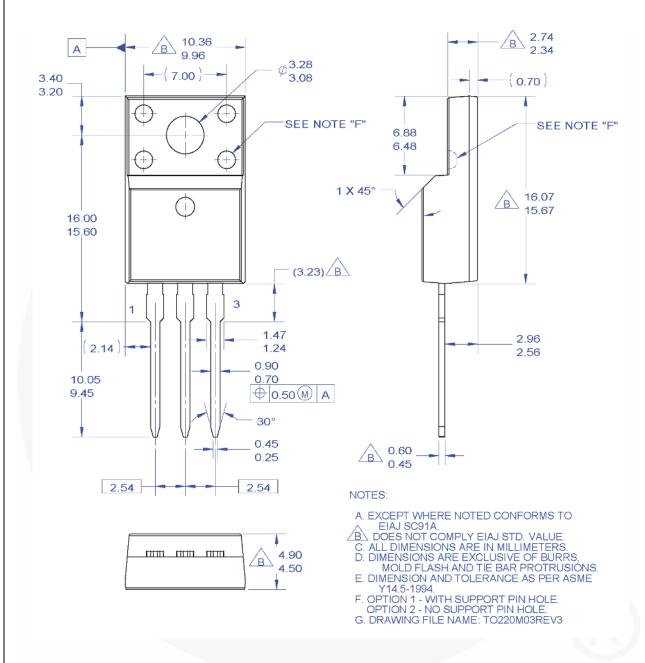


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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